



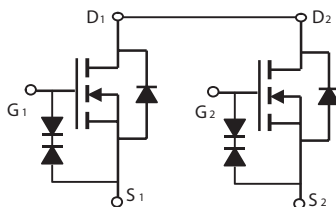
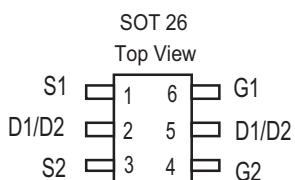
Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
20V	6A	20 @ V _{GS} =4.0V
		27 @ V _{GS} =2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±10	V
I _D	Drain Current-Continuous ^a	T _A =25°C	6
		T _A =70°C	4.8
I _{DM}	-Pulsed ^b	24	A
P _D	Maximum Power Dissipation ^a	T _A =25°C	1.25
		T _A =70°C	0.8
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	100	°C/W
------------------	--	-----	------

STS8216

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±10V , V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	0.5	0.8	1.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.0V , I _D =6A		17	20	m ohm
		V _{GS} =2.5V , I _D =5.2A		20	27	m ohm
g _{FS}	Forward Transconductance	V _{DS} =5V , I _D =6A		23		S
DYNAMIC CHARACTERISTICS ^c						
C _{iss}	Input Capacitance	V _{DS} =10V,V _{GS} =0V f=1.0MHz		470		pF
C _{oss}	Output Capacitance			164		pF
C _{rss}	Reverse Transfer Capacitance			142		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =10V I _D =1A V _{GS} =4.0V R _{GEN} =10 ohm		17		ns
t _r	Rise Time			54		ns
t _{D(OFF)}	Turn-Off Delay Time			63		ns
t _f	Fall Time			45		ns
Q _g	Total Gate Charge	V _{DS} =10V,I _D =6A, V _{GS} =4.0V		10		nC
Q _{gs}	Gate-Source Charge			2.1		nC
Q _{gd}	Gate-Drain Charge			4.5		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _s	Maximum Continuous Drain-Source Diode Forward Current				2.0	A
V _{SD}	Diode Forward Voltage ^b	V _{GS} =0V,I _s =2.0A		0.79	1.2	V

Notes

- a.Surface Mounted on FR4 Board,t ≤ 10sec.
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
c.Guaranteed by design, not subject to production testing.

Sep,11,2009

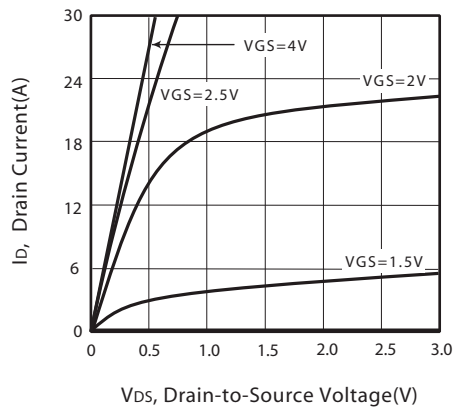


Figure 1. Output Characteristics

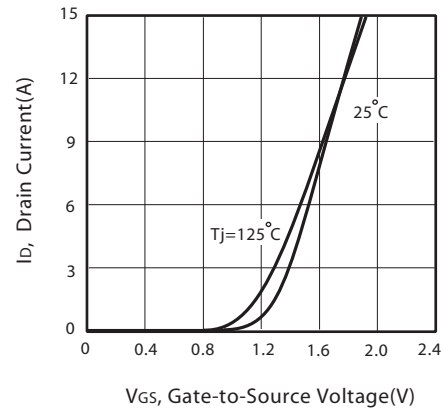


Figure 2. Transfer Characteristics

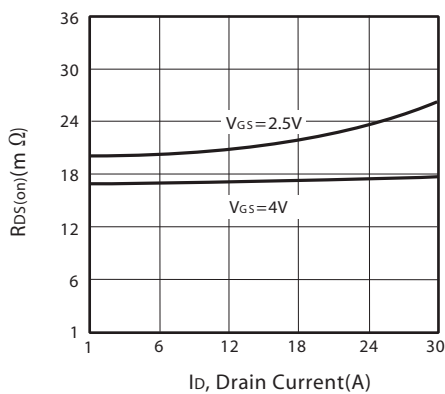


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

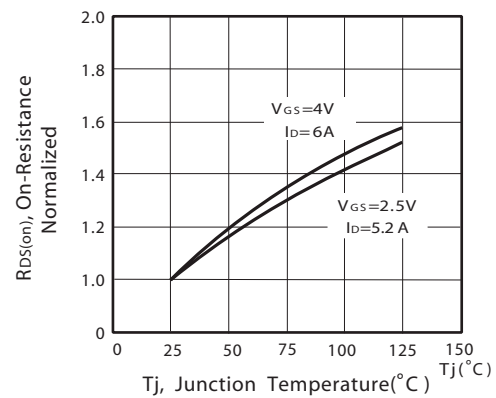


Figure 4. On-Resistance Variation with Drain Current and Temperature

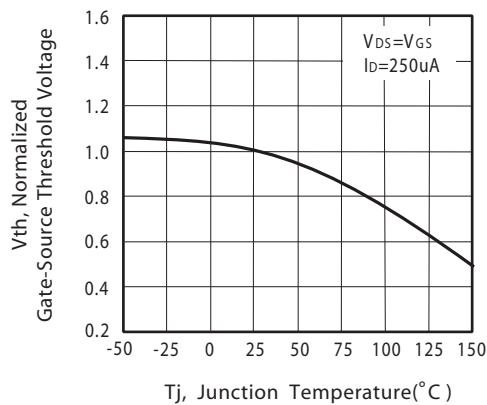


Figure 5. Gate Threshold Variation with Temperature

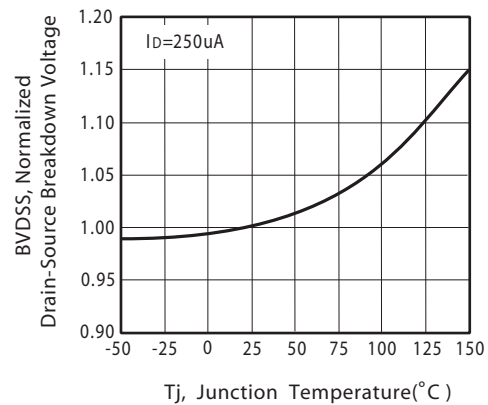


Figure 6. Breakdown Voltage Variation with Temperature

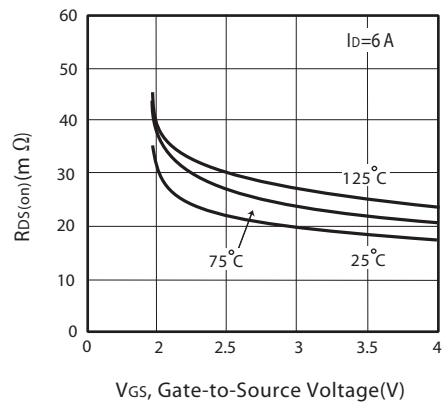


Figure 7. On-Resistance vs. Gate-Source Voltage

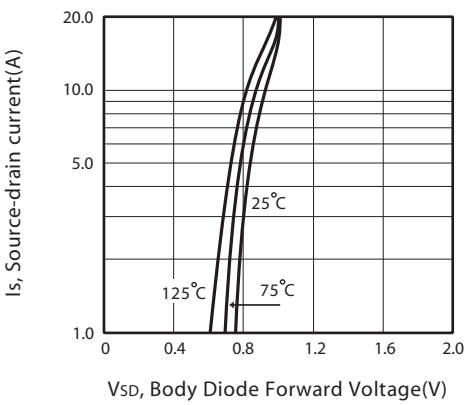


Figure 8. Body Diode Forward Voltage Variation with Source Current

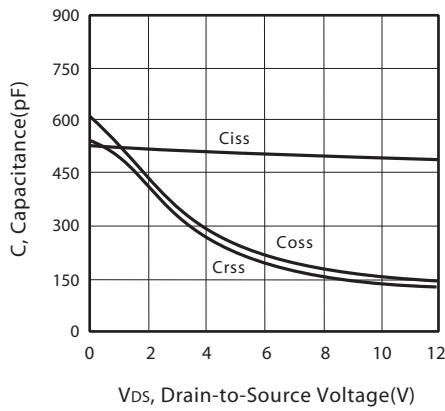


Figure 9. Capacitance

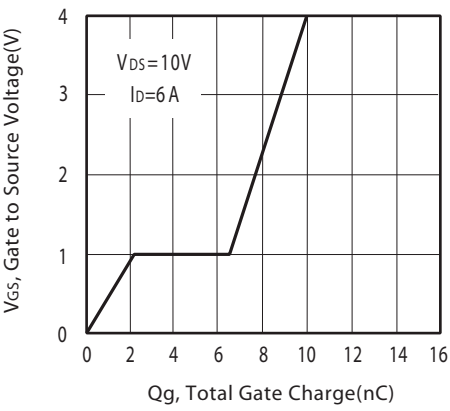


Figure 10. Gate Charge

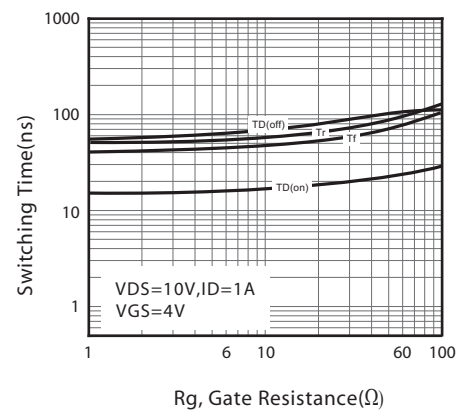


Figure 11. switching characteristics

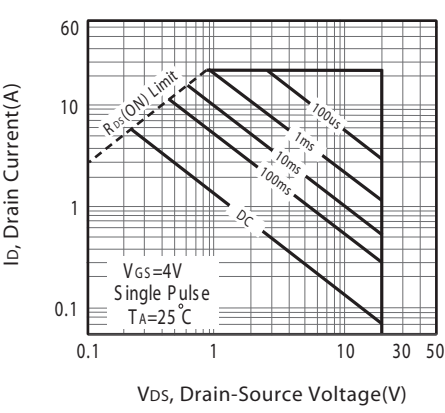


Figure 12. Maximum Safe Operating Area

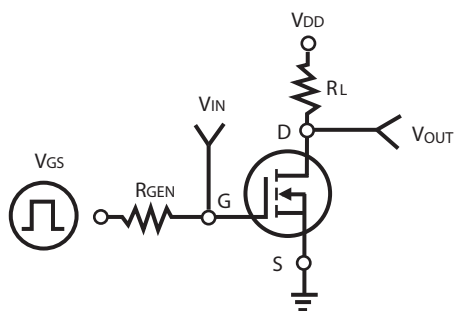


Figure 13. Switching Test Circuit

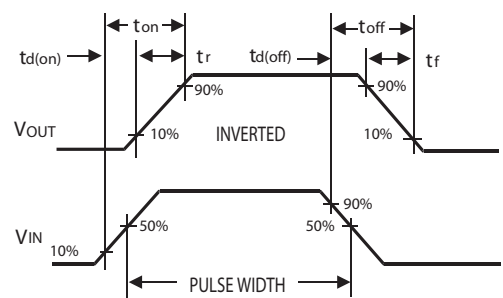
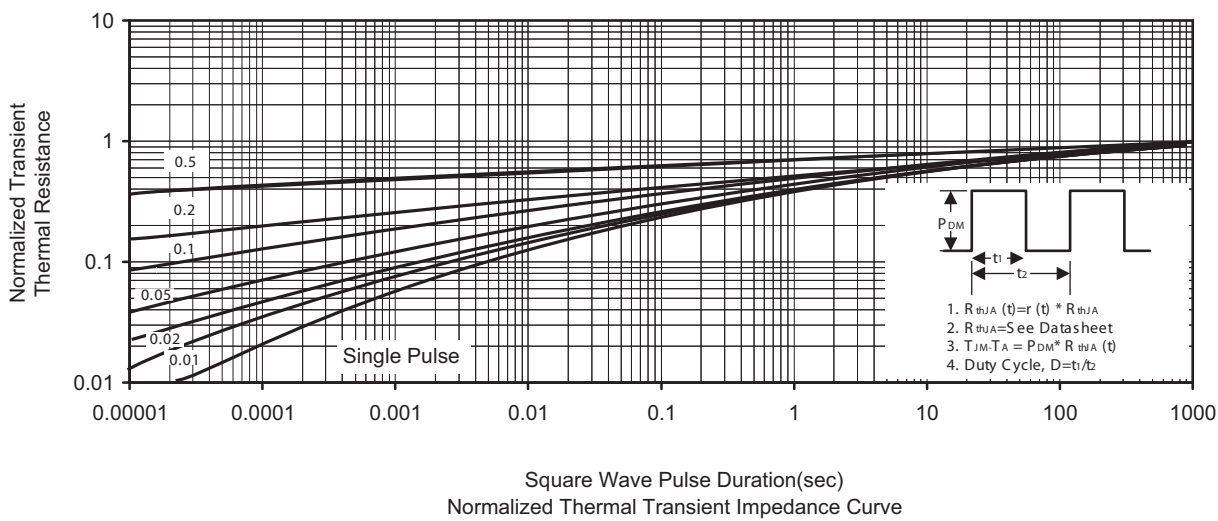
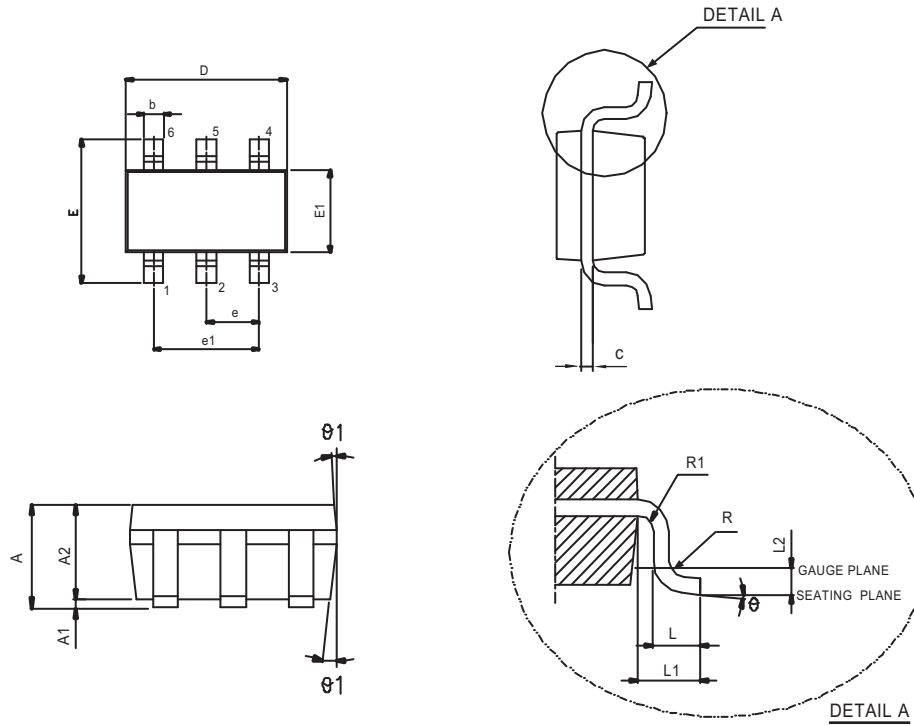


Figure 14. Switching Waveforms



PACKAGE OUTLINE DIMENSIONS

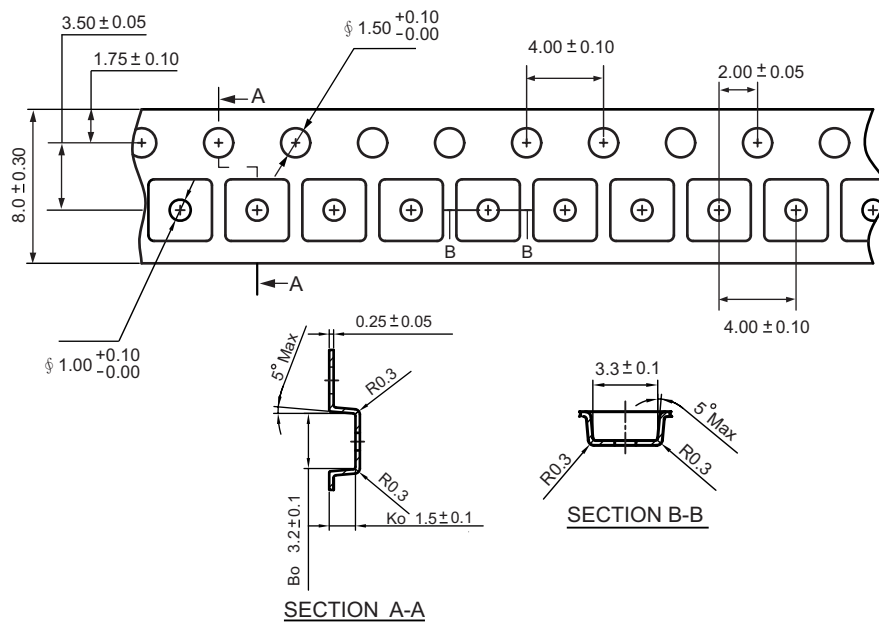
SOT 26



SYMBOL	MIN.	NOM.	MAX.
A	—	—	1.45
A1	—	—	0.15
A2	0.90	1.15	1.30
b	0.30	—	0.50
c	0.08	—	0.22
D	2.90 BSC.		
E	2.80 BSC.		
E1	1.60 BSC.		
e	0.95 BSC.		
e1	1.90 BSC.		
L	0.30	0.45	0.60
L1	0.60 REF.		
L2	0.25 BSC.		
R	0.10	—	—
R1	0.10	—	0.25
θ	0°	4°	8°
θ1	5°	10°	15°

SOT 26 Tape and Reel Data

SOT 26 Carrier Tape



SOT 26 Reel

